

SN74AHC1G02B-EP Enhanced Product, Single 2-Input Positive-NOR Gate

1 Features

- Operating range 2V to 5.5V V_{CC}
- Low delay, 4.3ns typ. (25°C, 5V)
- Latch-up performance exceeds 250mA per JESD 17
- Supports defense and aerospace applications:
 - Controlled baseline
 - One assembly and test site
 - One fabrication site
 - Extended product life cycle
 - Product traceability

2 Applications

- [Enable or disable a digital signal](#)
- [Controlling an indicator LED](#)

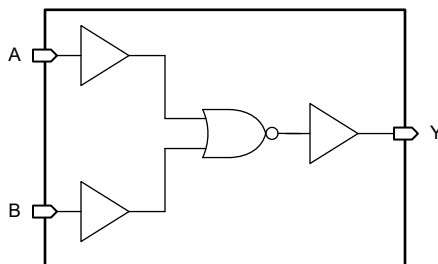
3 Description

The SN74AHC1G02B-EP is a 2-input NOR Gate which performs the Boolean function $Y = \overline{A + B}$ in positive logic.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾	BODY SIZE ⁽³⁾
SN74AHC1G02B-EP	DCK (SC-70, 5)	2.0mm × 2.1mm	2.0mm × 1.25mm

- (1) For more information, see the orderable addendum at the end of the data sheet.
- (2) The package size (length × width) is a nominal value and includes pins, where applicable
- (3) The body size (length × width) is a nominal value and does not include pins.



Logic Diagram (Positive Logic)



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4 Pin Configuration and Functions

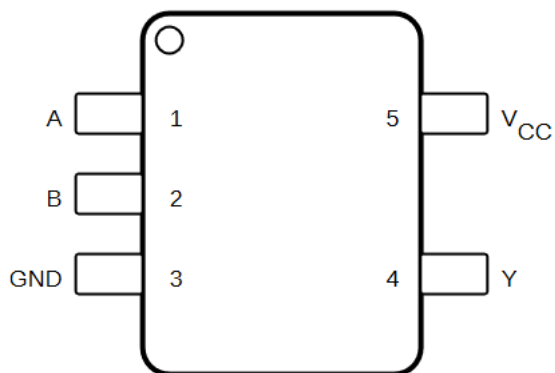


Figure 4-1. DCK Package 5-Pin SC70 (Top View)

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
A	1	I	Input A
B	2	I	Input B
GND	3	—	Ground Pin
Y	4	O	Output
V _{CC}	5	—	Supply Pin

(1) Signal Types: I = Input, O = Output, I/O = Input or Output

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V_{CC}	Supply voltage		-0.5	7	V
V_I	Input voltage range		-0.5	7	V
V_O	Output voltage range		-0.5	$V_{CC} + 0.5$	V
V_O	Voltage range applied to any output in the high-impedance or power-off state		-0.5	4.6	V
I_{IK}	Input clamp current ⁽²⁾	$V_I < 0$	-20		mA
I_{OK}	Output clamp current ⁽²⁾	$V_O < 0$ or $V_O > V_{CC}$	-20	20	mA
I_O	Continuous output current	$V_O = 0$ to V_{CC}	-25	25	mA
I_O	Continuous output current through V_{CC} or GND		-50	50	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		-65	150	°C

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged-device model (CDM), per ANSI/ESDA/ JEDEC JS-002 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
V_{CC}	Supply Voltage		2	5.5	V
V_{IH}	high-level input voltage	$V_{CC} = 2V$	1.5		V
V_{IH}	high-level input voltage	$V_{CC} = 3V$	2.1		V
V_{IH}	high-level input voltage	$V_{CC} = 5.5V$	3.85		V
V_{IL}	low-level input voltage	$V_{CC} = 2V$		0.5	V
V_{IL}	low-level input voltage	$V_{CC} = 3V$		0.9	V
V_{IL}	low-level input voltage	$V_{CC} = 5.5V$		1.65	V
V_I	input voltage		0	5.5	V
V_O	output voltage		0	V_{CC}	V
I_{OH}	high-level output current	$V_{CC} = 2V$		-50	μA
I_{OH}	high-level output current	$V_{CC} = 3.3V \pm 0.3V$		-4	mA
I_{OH}	high-level output current	$V_{CC} = 5V \pm 0.5V$		-8	mA
I_{OL}	low-level output current	$V_{CC} = 2V$		50	μA
I_{OL}	low-level output current	$V_{CC} = 3.3V \pm 0.3V$		4	mA
I_{OL}	low-level output current	$V_{CC} = 5V \pm 0.5V$		8	mA
$\Delta t/\Delta v$	input transition rise or fall rate	$V_{CC} = 3.3V \pm 0.3V$		100	nS/V
$\Delta t/\Delta v$	input transition rise or fall rate	$V_{CC} = 5V \pm 0.5V$		20	nS/V
T_A	Operating free-air temperature		-55	125	$^{\circ}C$

5.4 Thermal Information

PACKAGE	PINS	THERMAL METRIC ⁽¹⁾						UNIT
		$R_{\theta JA}$	$R_{\theta JC(top)}$	$R_{\theta JB}$	Ψ_{JT}	Ψ_{JB}	$R_{\theta JC(bot)}$	
DCK (SC-70)	5	329.6	244.7	217.7	142.1	216.7	-	$^{\circ}C/W$

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application note.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	T _A = 25°C			-40°C to 125°C			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V _{T+}	Positive-going input threshold voltage	V _{CC} = 3V	1.2		2.20	1.2		2.20	V
V _{T+}	Positive-going input threshold voltage	V _{CC} = 4.5V	1.75		3.15	1.75		3.15	V
V _{T+}	Positive-going input threshold voltage	V _{CC} = 5.5V	2.15		3.85	2.15		3.85	V
V _{T-}	Negative-going input threshold voltage	V _{CC} = 3V	0.9		1.9	0.9		1.9	V
V _{T-}	Negative-going input threshold voltage	V _{CC} = 4.5V	1.35		2.75	1.35		2.75	V
V _{T-}	Negative-going input threshold voltage	V _{CC} = 5.5V	1.65		3.35	1.65		3.35	V
ΔV _T	Hysteresis (V _{T+} - V _{T-})	V _{CC} = 3V	0.3		1.2	0.3		1.2	V
ΔV _T	Hysteresis (V _{T+} - V _{T-})	V _{CC} = 4.5V	0.4		1.4	0.4		1.4	V
ΔV _T	Hysteresis (V _{T+} - V _{T-})	V _{CC} = 5.5V	0.5		1.6	0.5		1.6	V
V _{OH}	I _{OH} = -50μA	V _{CC} = 2V	1.9			1.9			V
V _{OH}	I _{OH} = -50μA	V _{CC} = 3V	2.9			2.9			V
V _{OH}	I _{OH} = -50μA	V _{CC} = 4.5V	4.4			4.4			V
V _{OH}	I _{OH} = -4mA	V _{CC} = 3V	2.58			2.48			V
V _{OH}	I _{OH} = -8mA	V _{CC} = 4.5V	3.94			3.8			V
V _{OL}	I _{OH} = 50μA	V _{CC} = 2V			0.1			0.1	V
V _{OL}	I _{OH} = 50μA	V _{CC} = 3V			0.1			0.1	V
V _{OL}	I _{OH} = 50μA	V _{CC} = 4.5V			0.1			0.1	V
V _{OL}	I _{OH} = 4mA	V _{CC} = 3V			0.36			0.44	V
V _{OL}	I _{OH} = 8mA	V _{CC} = 4.5V			0.36			0.44	V
I _I	V _I = 5.5V or GND	0 V to 5.5V	-0.1		0.1	-1		1	μA
I _{OZ}	V _O = V _{CC} or GND	5.5V	-0.25		0.25	-2.5		2.5	μA
I _{CC}	V _I = V _{CC} or GND, I _O = 0	5.5V			1			4	μA
C _i	V _I = V _{CC} or GND	5V		1.7	10				pF
C _O	V _O = V _{CC} or GND	5V		3					pF
C _{PD}	Power dissipation capacitance	5V	5	14	22.4				pF

5.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	V_{CC}	-55°C to 125°C			UNIT
					MIN	TYP	MAX	
T_{PLH}	A or B	Y	CL = 15pF	3.3V ± 0.3V	1	5	9.5	nS
T_{PLH}	A or B	Y	CL = 50pF	3.3V ± 0.3V	1	7.5	13	nS
T_{PLH}	A or B	Y	CL = 15pF	5V ± 0.5V	1	3.6	7	nS
T_{PLH}	A or B	Y	CL = 50pF	5V ± 0.5V	1	5.1	7	nS
T_{PHL}	A or B	Y	CL = 15pF	3.3V ± 0.3V	1	5	9.5	nS
T_{PHL}	A or B	Y	CL = 50pF	3.3V ± 0.3V	1	7.5	13	nS
T_{PHL}	A or B	Y	CL = 15pF	5V ± 0.5V	1	3.6	7	nS
T_{PHL}	A or B	Y	CL = 50pF	5V ± 0.5V	1	5.1	7	nS
T_{PLH}	A or B	Y	CL = 15pF	3.3V ± 0.3V	1	3.6	8.5	nS
T_{PLH}	A or B	Y	CL = 50pF	3.3V ± 0.3V	1.5	6.5	12.5	nS
T_{PLH}	A or B	Y	CL = 15pF	5V ± 0.5V	1	2.5	6.5	nS
T_{PLH}	A or B	Y	CL = 50pF	5V ± 0.5V	1.5	4.6	8.5	nS
T_{PHL}	A or B	Y	CL = 15pF	3.3V ± 0.3V	1	3.6	8.5	nS
T_{PHL}	A or B	Y	CL = 50pF	3.3V ± 0.3V	1.5	6.5	12.5	nS
T_{PHL}	A or B	Y	CL = 15pF	5V ± 0.5V	1	2.5	6.5	nS
T_{PHL}	A or B	Y	CL = 50pF	5V ± 0.5V	1.5	4.6	8.5	nS
T_{PLH}	A or B	Y	CL = 15pF	3.3V ± 0.3V	1	7	14	nS
T_{PLH}	A or B	Y	CL = 50pF	3.3V ± 0.3V	1	9.5	17.5	nS
T_{PLH}	A or B	Y	CL = 15pF	5V ± 0.5V	1	4.8	8.6	nS
T_{PLH}	A or B	Y	CL = 50pF	5V ± 0.5V	1	6.3	11	nS
T_{PHL}	A or B	Y	CL = 15pF	3.3V ± 0.3V	1	7	14	nS
T_{PHL}	A or B	Y	CL = 50pF	3.3V ± 0.3V	1	9.5	17.5	nS
T_{PHL}	A or B	Y	CL = 15pF	5V ± 0.5V	1	4.8	8.6	nS
T_{PHL}	A or B	Y	CL = 50pF	5V ± 0.5V	1	6.3	11	nS

5.7 Typical Characteristics

$T_A = 25^\circ\text{C}$ (unless otherwise noted)

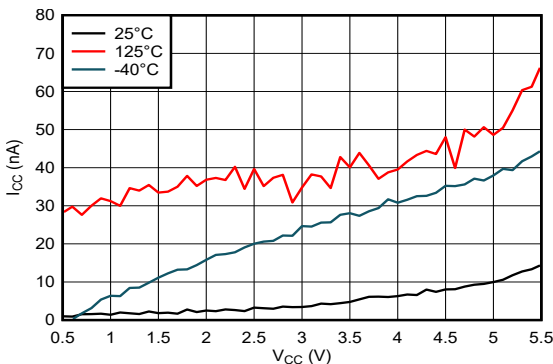


Figure 5-1. Supply Current Across Supply Voltage

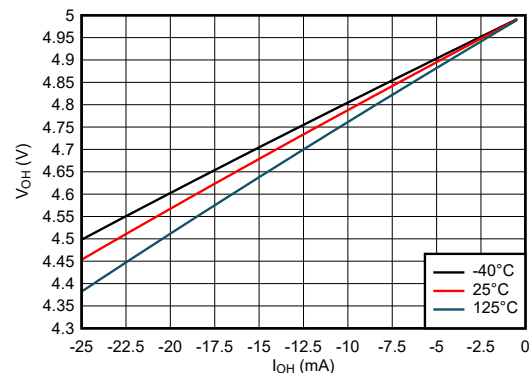


Figure 5-2. Output Voltage vs Current in HIGH State; 5V Supply

5.7 Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$ (unless otherwise noted)

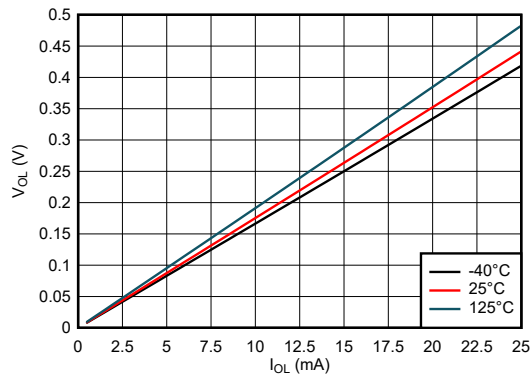


Figure 5-3. Output Voltage vs Current in LOW State; 5V Supply

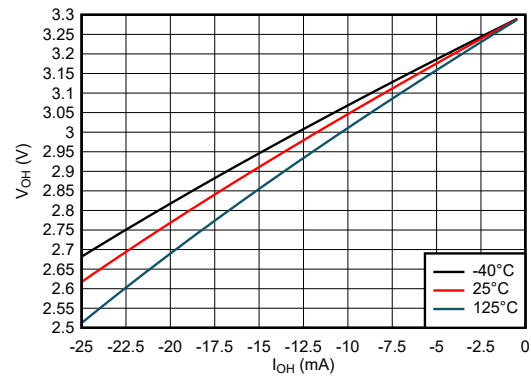


Figure 5-4. Output Voltage vs Current in HIGH State; 3.3V Supply

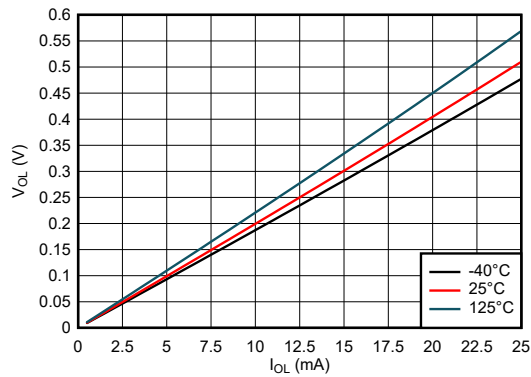


Figure 5-5. Output Voltage vs Current in LOW State; 3.3V Supply

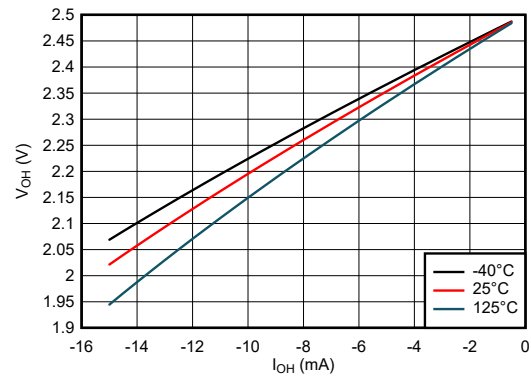


Figure 5-6. Output Voltage vs Current in HIGH State; 2.5V Supply

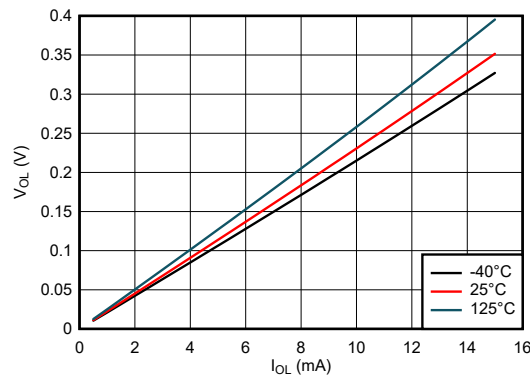
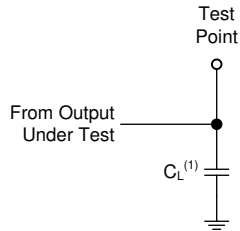


Figure 5-7. Output Voltage vs Current in LOW State; 2.5V Supply

6 Parameter Measurement Information

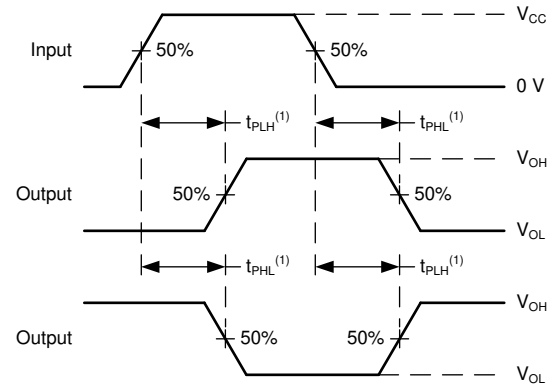
Phase relationships between waveforms were chosen arbitrarily for the examples listed in the following table. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1\text{MHz}$, $Z_O = 50\Omega$, $t_f < 2.5\text{ns}$.

The outputs are measured individually with one input transition per measurement.



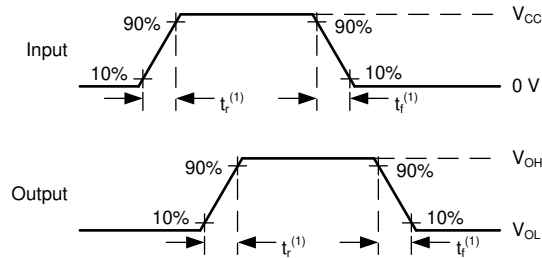
(1) C_L includes probe and test-fixture capacitance.

Figure 6-1. Load Circuit for Push-Pull Outputs



(1) The greater between $t_{PLH}^{(1)}$ and $t_{PHL}^{(1)}$ is the same as t_{pd} .

Figure 6-2. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t .

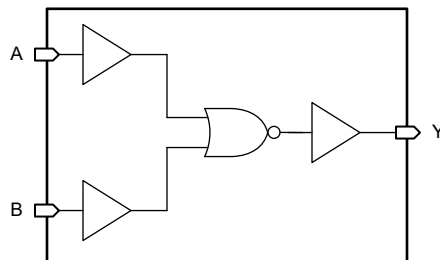
Figure 6-3. Voltage Waveforms, Input and Output Transition Times

7 Detailed Description

7.1 Overview

This device is a 2-input NOR Gate which performs the Boolean function $Y = \overline{A + B}$ in positive logic.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important to limit the output power of the device to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs must be left disconnected.

7.3.2 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law ($R = V \div I$).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in [Implications of Slow or Floating CMOS Inputs](#).

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a 10k Ω resistor, however, is recommended and will typically meet all requirements.

7.3.3 Clamp Diode Structure

As [Figure 7-1](#) shows, the outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

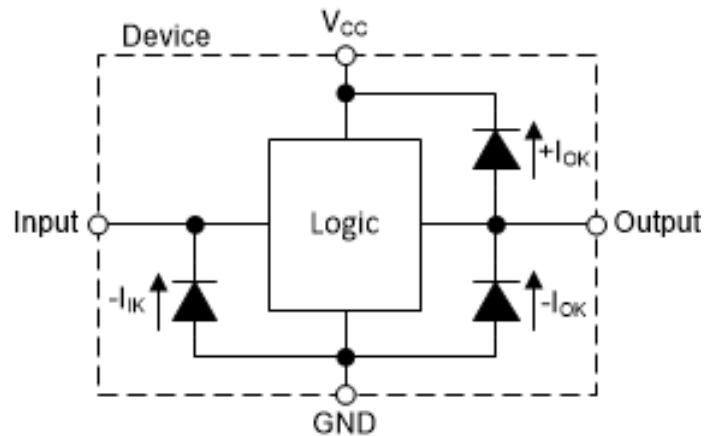


Figure 7-1. Electrical Placement of Clamping Diodes for Each Input and Output

7.4 Device Functional Modes

Table 7-1 lists the functional modes of the SN74AHC1G02B-EP.

Table 7-1. Function Table

INPUTS ⁽¹⁾		OUTPUT
A	B	Y
L	L	H
H	X	L
X	H	L

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

In this application, a couple of 2-input NOR gates are used to create an SR latch as shown in [Figure 8-1](#).

The SN74AHC1G02B-EP is used to drive the tamper indicator LED and provide one bit of data to the system controller. When the tamper switch outputs HIGH, the output Q becomes HIGH. This output remains HIGH until the system controller addresses the event and sends a HIGH signal to the R input which returns the Q output back to LOW.

8.2 Typical Application

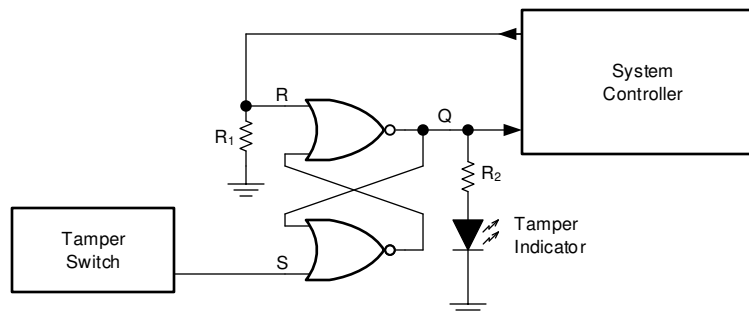


Figure 8-1. Typical Application Block Diagram

8.2.1 Design Requirements

8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics of the device as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74AHC1G02B-EP plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Ensure the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings* is not exceeded.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74AHC1G02B-EP plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Ensure the maximum total current through GND listed in the *Absolute Maximum Ratings* is not exceeded.

The SN74AHC1G02B-EP can drive a load with a total capacitance less than or equal to 50pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50pF.

The SN74AHC1G02B-EP can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

8.2.1.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74AHC1G02B-EP (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10k Ω resistor value is often used due to these factors.

The SN74AHC1G02B-EP has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

8.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is $\leq 50\text{pF}$. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74AHC1G02B-EP to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)})\Omega$. Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in $\text{M}\Omega$; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

8.2.3 Application Curves

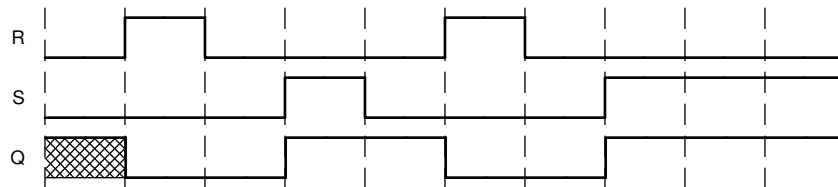


Figure 8-2. Application Timing Diagram

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions*.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For the SN74AHC1G02B-EP, a $0.1\mu\text{F}$ bypass capacitor is recommended. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of $0.1\mu\text{F}$ and $1\mu\text{F}$ are commonly used in parallel.

8.4 Layout

8.4.1 Layout Guidelines

- Bypass capacitor placement
 - Place near the positive supply terminal of the device
 - Provide an electrically short ground return path
 - Use wide traces to minimize impedance
 - Keep the device, capacitors, and traces on the same side of the board whenever possible
- Signal trace geometry
 - 8mil to 12mil trace width
 - Lengths less than 12cm to minimize transmission line effects
 - Avoid 90° corners for signal traces
 - Use an unbroken ground plane below signal traces
 - Flood fill areas around signal traces with ground
 - For traces longer than 12cm
 - Use impedance controlled traces
 - Source-terminate using a series damping resistor near the output
 - Avoid branches; buffer signals that must branch separately

8.4.2 Layout Example

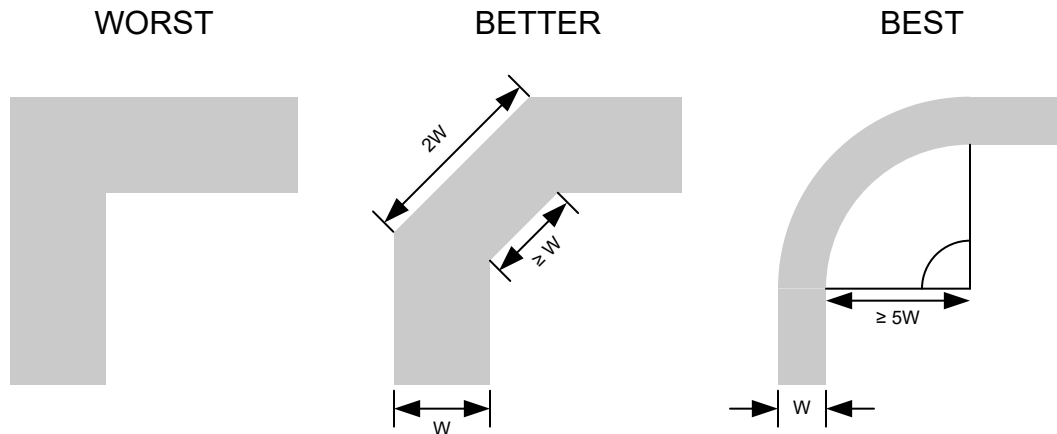


Figure 8-3. Example Trace Corners for Improved Signal Integrity

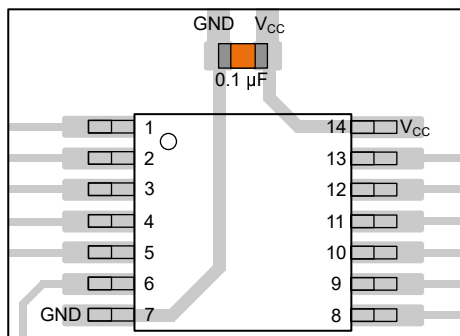


Figure 8-4. Example Bypass Capacitor Placement for TSSOP and Similar Packages

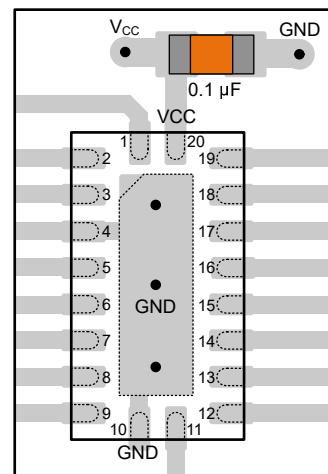


Figure 8-5. Example Bypass Capacitor Placement for WQFN and Similar Packages

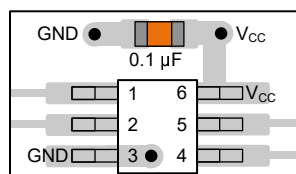


Figure 8-6. Example Bypass Capacitor Placement for SOT, SC70 and Similar Packages

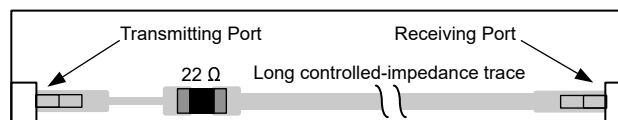


Figure 8-7. Example Damping Resistor Placement for Improved Signal Integrity

9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and \$C_{pd}\$ Calculation application report](#)
- Texas Instruments, [Designing With Logic application report](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application report](#)

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](https://www.ti.com). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ [support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.4 Trademarks

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9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

DATE	REVISION	NOTES
March 2025	*	Initial Release

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CAHC1G02BMDCKREP	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CGC
CAHC1G02BMDCKREP.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CGC

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CAHC1G02BMDCKREP	SC70	DCK	5	3000	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS

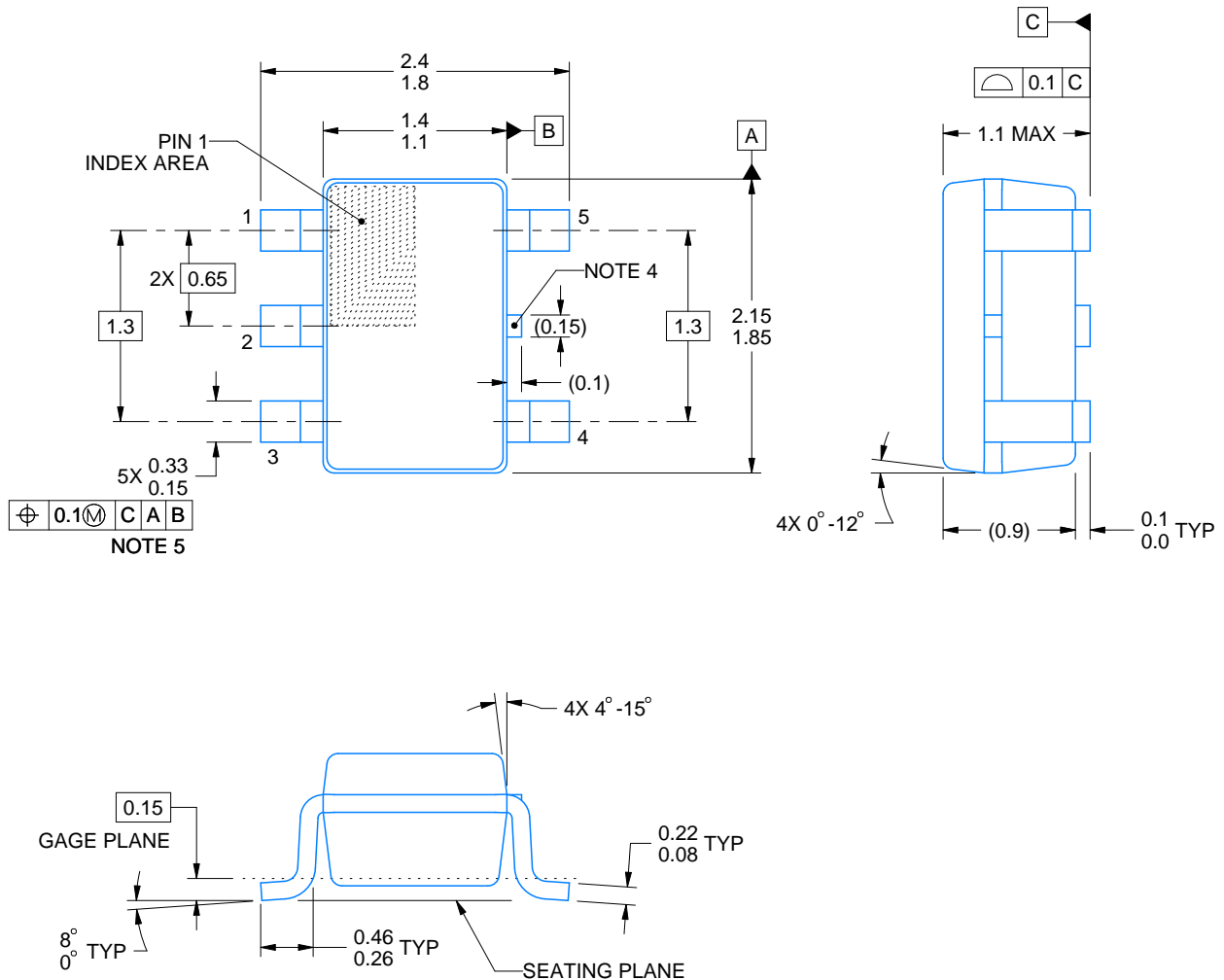


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CAHC1G02BMDCKREP	SC70	DCK	5	3000	202.0	201.0	28.0

DCK0005A**PACKAGE OUTLINE****SOT - 1.1 max height**

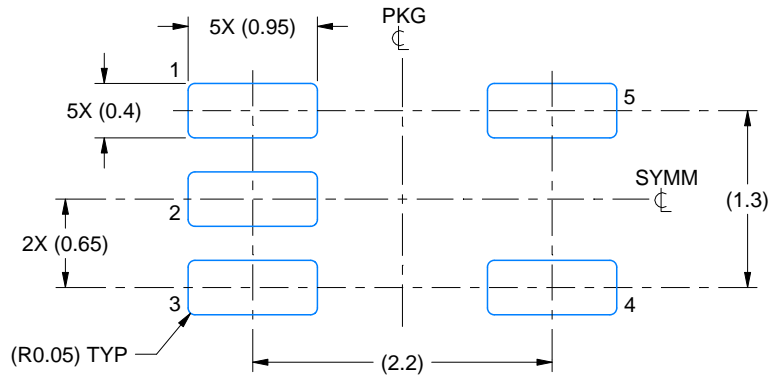
SMALL OUTLINE TRANSISTOR



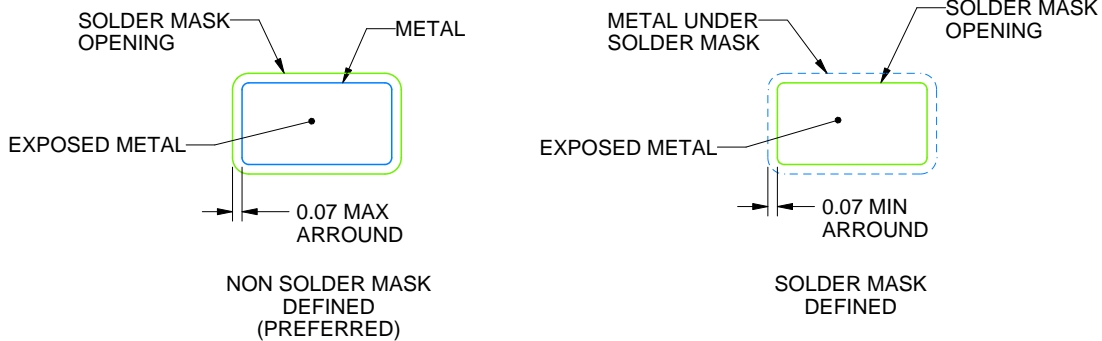
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NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

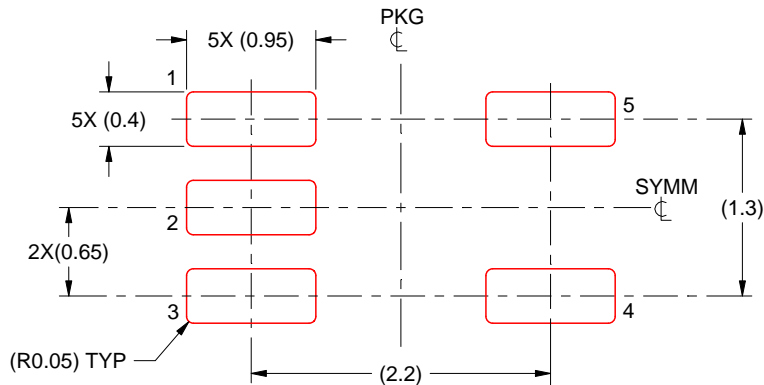


SOLDER MASK DETAILS

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NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

4214834/G 11/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

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